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# Publisher Correction: Stateful characterization of resistive switching $\text{TiO}_2$ with electron beam induced currents

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The original version of this Article contained an error in Eq. 1. The arrows between the symbols “T” and “B”, and “B” and “T”, were written “ $\leftrightarrow$ ” but should have been “ $\rightarrow$ ”, and incorrectly read:

$$I_{\text{EBIC}} = I_{\text{EBAC}} + I_{\text{SEE}} + I_{(\text{e} \leftrightarrow \text{h})} + I_{\text{ISEE}}^{\text{T} \leftrightarrow \text{B}} + I_{\text{ISEE}}^{\text{B} \leftrightarrow \text{T}}$$

The correct form of the Eq. 1 is as follows:

$$I_{\text{EBIC}} = I_{\text{EBAC}} + I_{\text{SEE}} + I_{(\text{e} \leftrightarrow \text{h})} + I_{\text{ISEE}}^{\text{T} \rightarrow \text{B}} + I_{\text{ISEE}}^{\text{B} \rightarrow \text{T}}$$

This has now been corrected in both the PDF and HTML versions of the article.

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